

MOSFETs Silicon N-Channel MOS (U-MOSVI-H)

# TK50P04M1

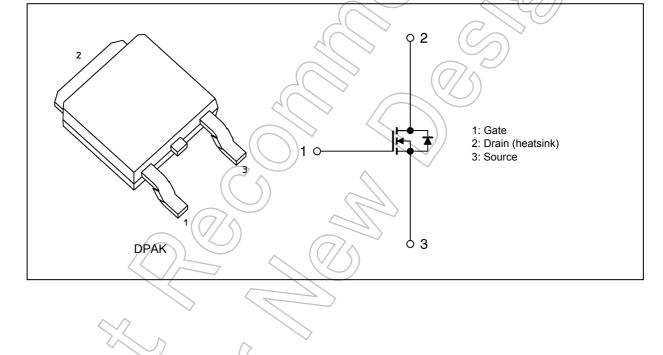
#### 1. Applications

- Switching Voltage Regulators
- · Motor Drivers
- · Power Management Switches

#### 2. Features

- (1) High-speed switching
- (2) Low gate charge:  $Q_{SW} = 9.4 \text{ nC (typ.)}$
- (3) Low drain-source on-resistance:  $R_{DS(ON)} = 6.7 \text{ m}\Omega$  (typ.) ( $V_{GS} = 10 \text{ V}$ )
- (4) Low leakage current:  $I_{DSS}$  = 10  $\mu A$  (max) ( $V_{DS}$  = 40 V)
- (5) Enhancement mode:  $V_{th} = 1.3 \text{ to } 2.3 \text{ V } (V_{DS} = 10 \text{ V}, I_D = 0.5 \text{ mA})$

#### 3. Packaging and Internal Circuit





## 4. Absolute Maximum Ratings (Note) (Ta = 25°C unless otherwise specified)

| Characteristics                | Symbol                  | Rating   | Unit             |            |    |
|--------------------------------|-------------------------|----------|------------------|------------|----|
| Drain-source voltage           |                         |          | V <sub>DSS</sub> | 40         | V  |
| Gate-source voltage            |                         |          | V <sub>GSS</sub> | ±20        |    |
| Drain current (DC)             |                         | (Note 1) | I <sub>D</sub>   | 50         | Α  |
| Drain current (pulsed)         |                         | (Note 1) | I <sub>DP</sub>  | 150        |    |
| Power dissipation              | (T <sub>c</sub> = 25°C) |          | P <sub>D</sub>   | 60         | W  |
| Single-pulse avalanche energy  |                         | (Note 2) | E <sub>AS</sub>  | 65         | mJ |
| Single-pulse avalanche current |                         |          | IAS              | 50         | Α  |
| Channel temperature            |                         | 4        | T <sub>ch</sub>  | 150        | °C |
| Storage temperature            |                         |          | T <sub>stg</sub> | -55 to 150 |    |

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

#### 5. Thermal Characteristics

| Char                                  | racteristics | Symbol                | Max  | Unit |
|---------------------------------------|--------------|-----------------------|------|------|
| Channel-to-case thermal resistance    | 2(\)         | R <sub>th(ch-c)</sub> | 2.08 | °C/W |
| Channel-to-ambient thermal resistance | 4( )         | R <sub>th(ch-a)</sub> | 125  |      |

Note 1: Ensure that the channel temperature does not exceed 150°C.

Note 2:  $V_{DD}$  = 32 V,  $T_{ch}$  = 25°C (initial), L = 20  $\mu$ H,  $R_{G}$  = 1.2  $\Omega$ ,  $I_{AS}$  = 50 A

Note: This transistor is sensitive to electrostatic discharge and should be handled with care.



#### 6. Electrical Characteristics

### 6.1. Static Characteristics (T<sub>a</sub> = 25°C unless otherwise specified)

| Characteristics                | Symbol               | Test Condition                                    | Min           | Тур.           | Max  | Unit |
|--------------------------------|----------------------|---|---------------|----------------|------|------|
| Gate leakage current           | I <sub>GSS</sub>     | $V_{GS} = \pm 20 \text{ V}, V_{DS} = 0 \text{ V}$ | _             | _              | ±0.1 | μА   |
| Drain cut-off current          | I <sub>DSS</sub>     | V <sub>DS</sub> = 40 V, V <sub>GS</sub> = 0 V     | 7             | _              | 10   |      |
| Drain-source breakdown voltage | V <sub>(BR)DSS</sub> | I <sub>D</sub> = 10 mA, V <sub>GS</sub> = 0 V     | 40            | _              | _    | V    |
|                                | V <sub>(BR)DSX</sub> | I <sub>D</sub> = 10 mA, V <sub>GS</sub> = -20 V   | 25            | ) <del>}</del> |      |      |
| Gate threshold voltage         | $V_{th}$             | V <sub>DS</sub> = 10 V, I <sub>D</sub> = 0.5 mA   | 1.3           | /_             | 2.3  |      |
| Drain-source on-resistance     | R <sub>DS(ON)</sub>  | V <sub>GS</sub> = 4.5 V, I <sub>D</sub> = 25 A    | /             | 7.8            | 10.2 | mΩ   |
|                                |                      | V <sub>GS</sub> = 10 V, I <sub>D</sub> = 25 A     | $\mathcal{L}$ | 6.7            | 8.7  |      |

### 6.2. Dynamic Characteristics (T<sub>a</sub> = 25°C unless otherwise specified)

| Characteristics                | Symbol           | Test Condition   | Min    | Тур. | Max | Unit |
|--------------------------------|------------------|--|--------|------|-----|------|
| Input capacitance              | C <sub>iss</sub> | V <sub>DS</sub> = 10 V, V <sub>GS</sub> = 0 V, f = 1 MHz |        | 2600 | _   | pF   |
| Reverse transfer capacitance   | C <sub>rss</sub> |  | _((    | 110  | _   |      |
| Output capacitance             | C <sub>oss</sub> |  | 7      | 420  | ) — |      |
| Gate resistance                | r <sub>g</sub>   | V <sub>DS</sub> = 10 V, V <sub>GS</sub> = 0 V, f = 5 MHz |        | 2.5  | 3.8 | Ω    |
| Switching time (rise time)     | t <sub>r</sub>   | See Figure 6.2.1.  |        | 22   | _   | ns   |
| Switching time (turn-on time)  | t <sub>on</sub>  |  | //-//  | 29   | _   |      |
| Switching time (fall time)     | t <sub>f</sub>   |  | $\sim$ | 10   | _   |      |
| Switching time (turn-off time) | t <sub>off</sub> |  | リー     | 77   | _   |      |

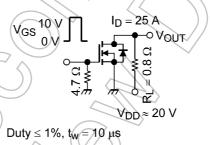


Fig. 6.2.1 Switching Time Test Circuit

# 6.3. Gate Charge Characteristics ( $T_a = 25^{\circ}$ C unless otherwise specified)

| Characteristics                     | Symbol           | Test Condition  | Min | Тур. | Max | Unit |
|-------------------------------------|------------------|---|-----|------|-----|------|
| Total gate charge (gate-source plus | Qg               | $V_{DD} \approx 32 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 50 \text{ A}$  | _   | 38   |     | nC   |
| gate-drain)                         |                  | $V_{DD} \approx 32 \text{ V}, V_{GS} = 5 \text{ V}, I_{D} = 50 \text{ A}$ |     | 20   |     |      |
| Gate-source charge 1                | Q <sub>gs1</sub> | $V_{DD} \approx 32 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 50 \text{ A}$  |     | 8.0  |     |      |
| Gate-drain charge                   | $Q_{gd}$         |   | _   | 5.7  |     |      |
| Gate switch charge                  | Q <sub>SW</sub>  |   | _   | 9.4  |     |      |

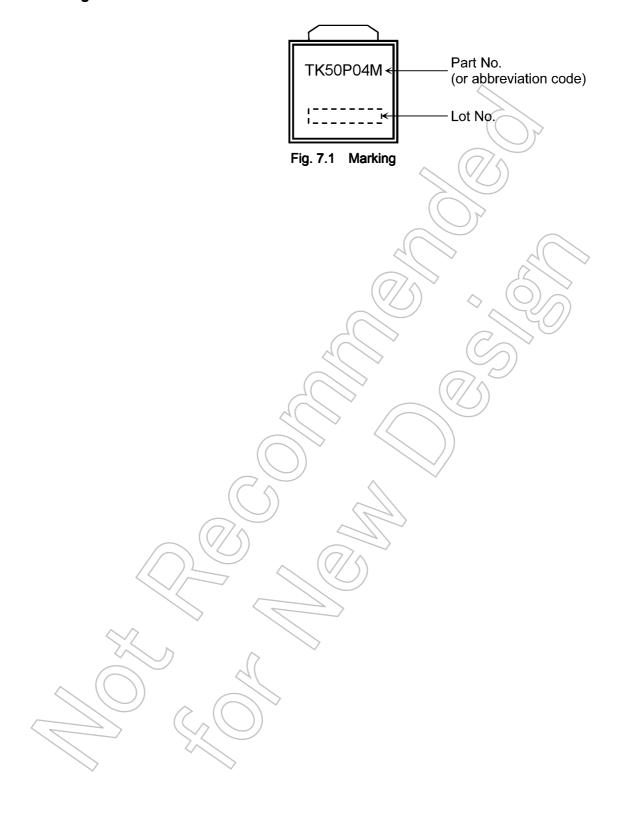
### 6.4. Source-Drain Characteristics (T<sub>a</sub> = 25°C unless otherwise specified)

| Characteristics                         | Symbol           | Test Condition                                | Min | Тур. | Max  | Unit |
|---|------------------|---|-----|------|------|------|
| Reverse drain current (pulsed) (Note 3) | I <sub>DRP</sub> | _   | _   | _    | 150  | Α    |
| Diode forward voltage                   | V <sub>DSF</sub> | I <sub>DR</sub> = 50 A, V <sub>GS</sub> = 0 V | _   | _    | -1.2 | V    |

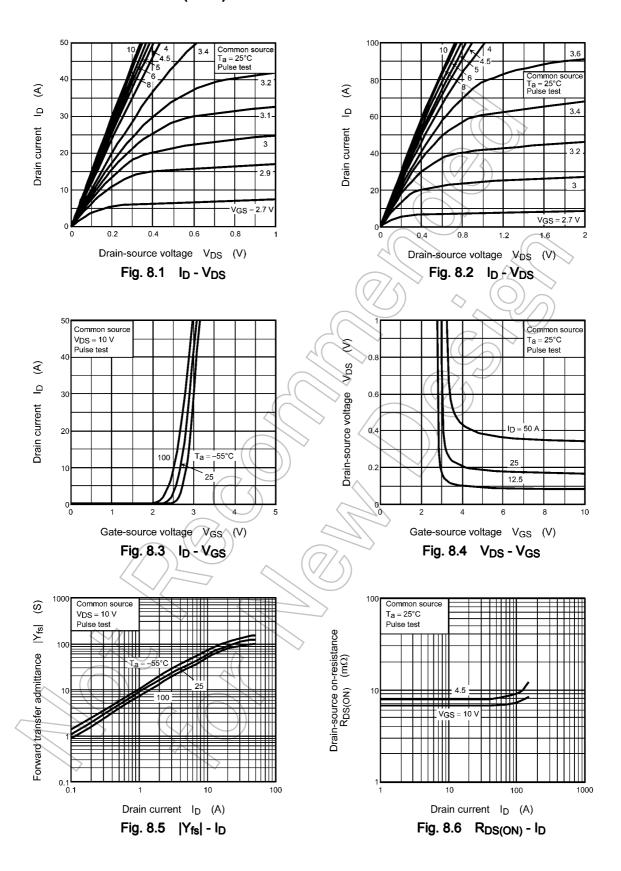
Note 3: Ensure that the channel temperature does not exceed 150°C.



### 7. Marking



#### 8. Characteristics Curves (Note)



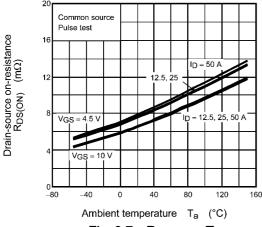


Fig. 8.7 R<sub>DS(ON)</sub> - T<sub>a</sub>

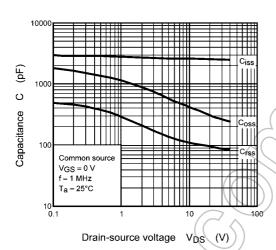


Fig. 8.9 Capacitance - V<sub>DS</sub>

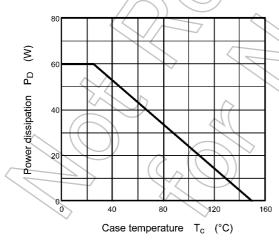


Fig. 8.11 P<sub>D</sub> - T<sub>c</sub> (Guaranteed Maximum)

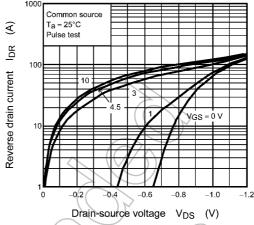


Fig. 8.8 IDR - VDS

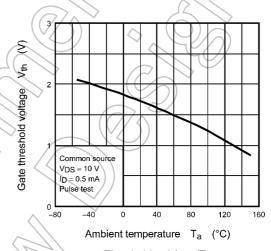


Fig. 8.10 V<sub>th</sub> - T<sub>a</sub>

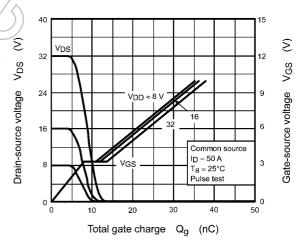
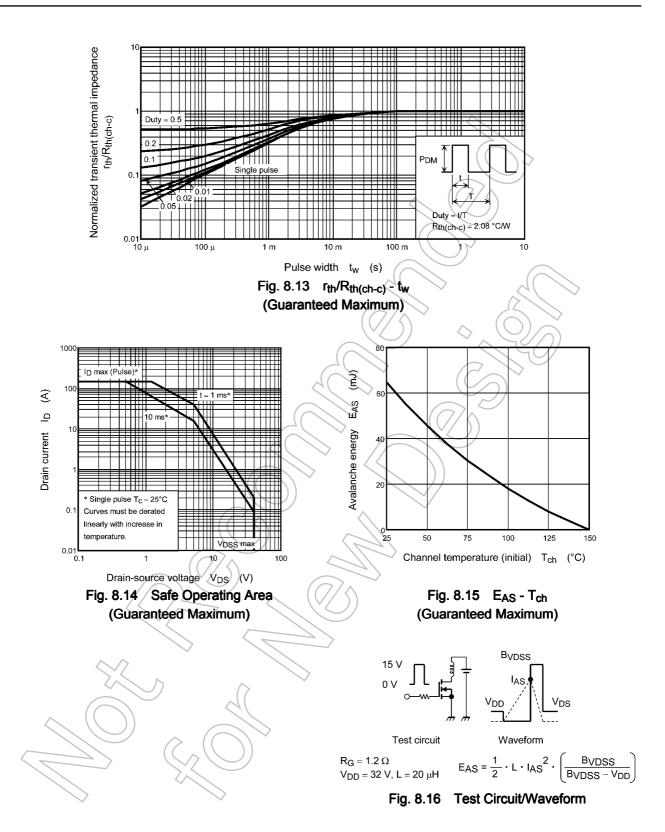


Fig. 8.12 Dynamic Input/Output Characteristics

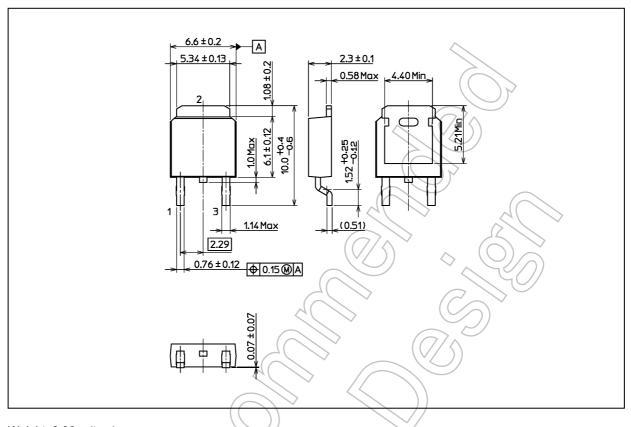


Note: The above characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.

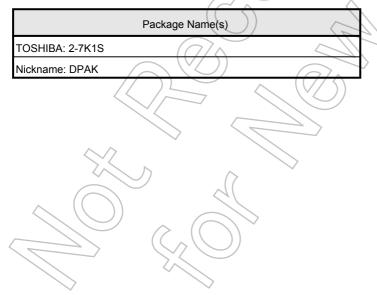


### **Package Dimensions**

Unit: mm



Weight: 0.36 g (typ.)





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